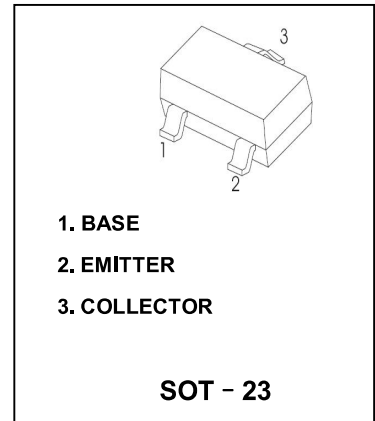


Plastic-Encapsulate Transistors

TRANSISTOR(NPN)

FEATURES

- High Voltage Application
- Telephone Application
- Complementary to MMBTA93


MARKING:2D
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	200	V
V _{CEO}	Collector-Emitter Voltage	200	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	500	mA
P _C	Collector Power Dissipation	350	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	357	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

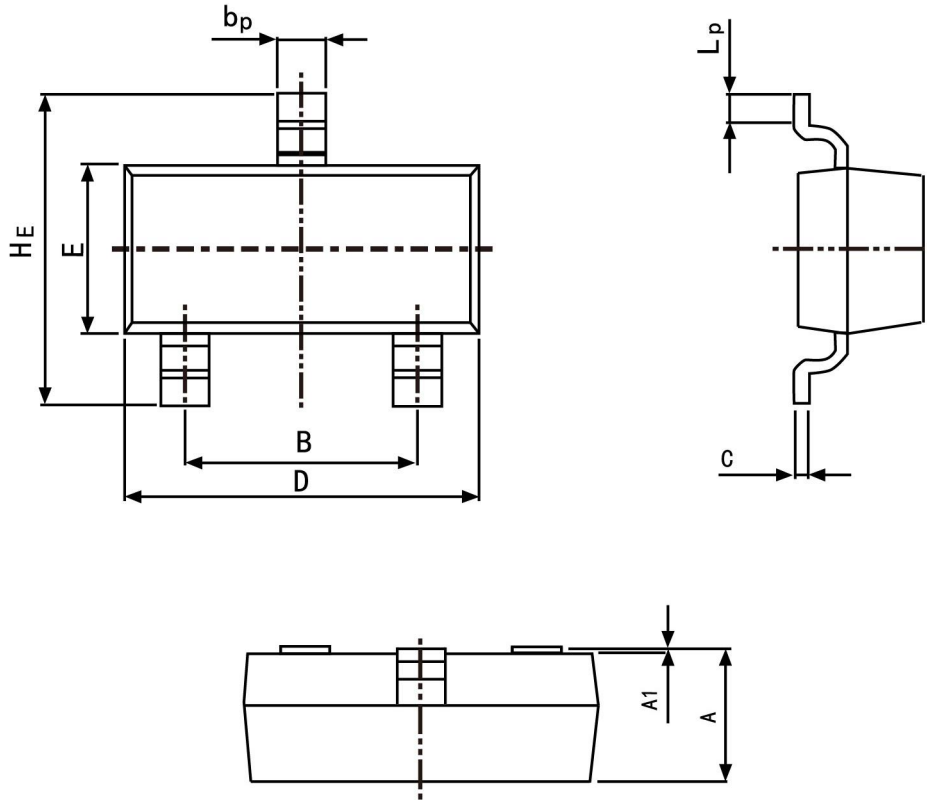
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	200			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	200			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA, I _C =0	5			V
DC current gain	h _{FE(1)} *	V _{CE} =10V, I _C =10mA	40			
	h _{FE(2)} *	V _{CE} =10V, I _C =1mA	40			
	h _{FE(3)} *	V _{CE} =10V, I _C =30mA	40			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =20mA, I _B =2mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =20mA, I _B =2mA			0.9	V
Transition frequency	f _T	V _{CE} =20V, I _E =10mA, f=100MHz	50			MHz
Collector output capacitance	C _{ob}	V _{CB} =20V, I _E =0, f=1MHz			4	pF

*Pulse test: pulse width ≤300μs, duty cycle ≤ 2.0%.

Package Outline

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-23	Tape/Reel, 7" reel	3 000	EIA-481-1

单击下面可查看定价，库存，交付和生命周期等信息

[>>YFW\(佑风微\)](#)